Abstracts

An Ultra Low Transient GaAs FET VHF Switch

D.W. White. "An Ultra Low Transient GaAs FET VHF Switch." 1984 MTT-S International Microwave Symposium Digest 84.1 (1984 [MWSYM]): 155-157.

A simple unbalanced GaAs FET switch is described which has 20 dB lower peak transients than commercial balanced diode designs. An auto-transformer neutralization circuit provides more than 55 dB off-isolation over a three octave bandwidth. A novel scheme which derives both drive and bias from Schottky TTL gates eliminates the bipolar supplies and discrete drive circuitry usually found in high speed switches. A low level transient caused by carrier trapping in the GaAs material is described.

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